



Supplementary Material

# Pseudo-Interface Switching of a Two-Terminal TaO<sub>x</sub>/HfO<sub>2</sub> Synaptic Device for Neuromorphic Applications

Hojeong Ryu and Sungjun Kim \*

Division of Electronics and Electrical Engineering, Dongguk University, Seoul 04620, Korea;  
hojeong.ryu@dongguk.edu

\* Correspondence: sungjun@dongguk.edu

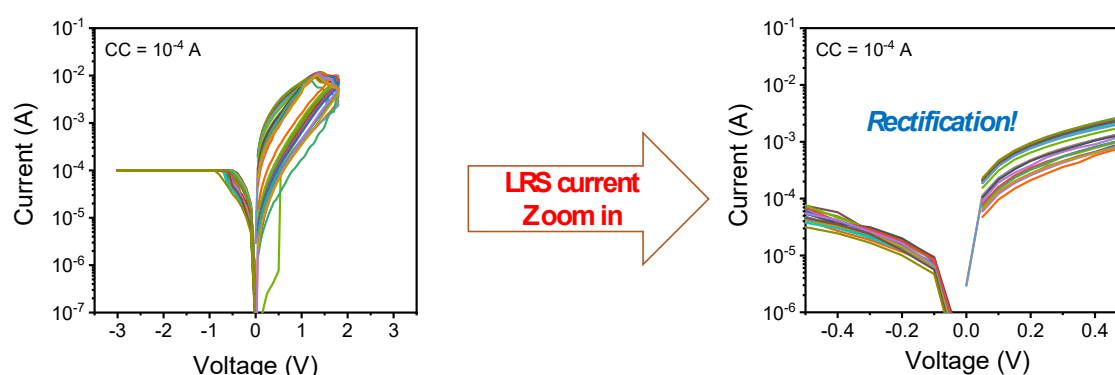


Figure S1. Rectifying I-V characteristics of the TaO<sub>x</sub>/HfO<sub>2</sub> memristor in the LRS at CC of 10<sup>-4</sup> A.

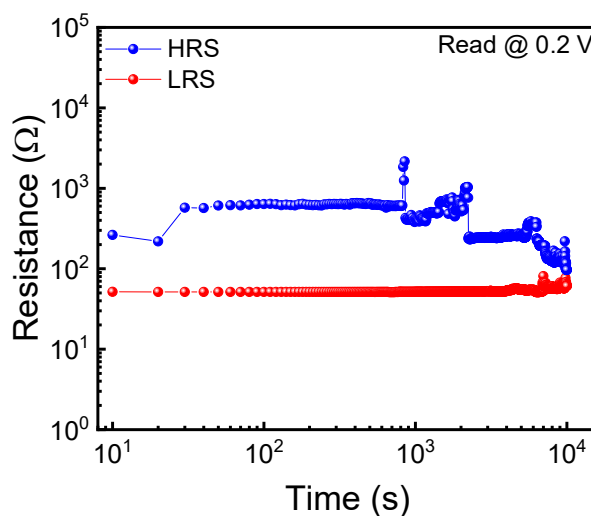


Figure S2. Retention test for interface-type switching of the TaO<sub>x</sub>/HfO<sub>2</sub> memristor.



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